

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Surface-mounted package
- Low Thermal Resistance
- ESD 2KV

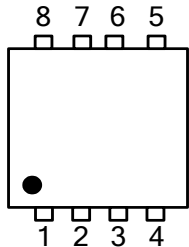
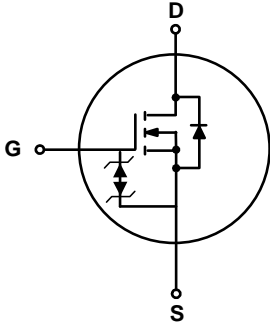
1.2 Applications

- Motor drivers
- DC - DC Converter

1.3 Quick reference

- $BV \geq 20\text{ V}$
- $R_{DS(ON)} \leq 9.5\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- $P_{tot} \leq 20.8\text{ W}$
- $R_{DS(ON)} \leq 13\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- $I_D \leq 38\text{ A}$
- $R_{DS(ON)} \leq 20\text{ m}\Omega @ V_{GS} = 1.8\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 <p>Top View PDFN3.3x3.3-8L</p>	
4	Gate		
5,6,7,8	Drain		



3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	20	-	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	± 10	V
I _D *	Drain Current	T _C = 25 °C, V _{GS} = 4.5 V	-	38	A
		T _C = 100 °C, V _{GS} = 4.5 V	-	23.5	A
I _{DM} *,**,***	Pulsed Source Current	T _C = 25 °C, V _{GS} = 4.5 V	-	112	A
P _{tot} *	Total Power Dissipation	T _C = 25 °C	-	20.8	W
T _{stg}	Storage Temperature		- 55	150	°C
T _J	Junction Temperature		-	150	°C
I _S	Diode Forward Current	T _C = 25 °C	-	38	A
E _{AS} *	Single Pulsed Avalanche Energy	V _{DD} = 20 V , L= 1.0 mH	-	66	mJ
R _{θJA} *	Thermal Resistance- Junction to Ambient		-	62.5	°C / W
R _{θJC} *	Thermal Resistance- Junction to Case		-	6	

Notes :

- * Surface Mounted on 1 in² pad area, t ≤ 10 sec
- ** Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ2008Q	<div style="display: inline-block; border: 1px solid black; padding: 2px;">2008 YWWXXX</div> YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ2008Q	PDFN3.3*3.3			5000	

Note: KUAJIEXIN defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

6. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

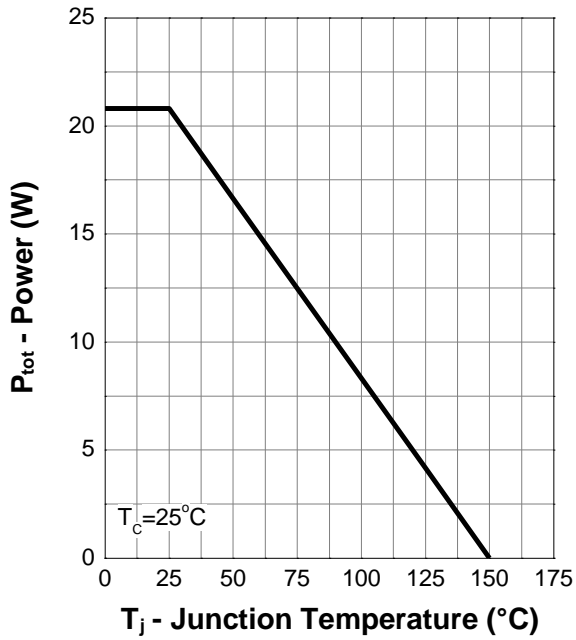
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	20	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	0.5	-	1	V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} = 16 V, V _{GS} = 0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 10 V, V _{DS} = 0 V	-	-	± 10	uA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} = 4.5 V, I _D = 5 A	-	8.5	9.5	m Ω
		V _{GS} = 2.5 V, I _D = 3 A	-	11	13	
		V _{GS} = 1.8 V, I _D = 2 A	-	16	20	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} = 5 A, V _{GS} = 0 V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} = 5 A, dI _{SD} /dt = 100 A/μs	-	25	-	nS
Q _{rr}	Reverse Recovery Charge		-	10.5	-	nC
Dynamic Characteristics^b						
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 10 V Frequency = 1 MHz	-	998	-	pF
C _{oss}	Output Capacitance		-	131	-	
C _{rss}	Reverse Transfer Capacitance		-	125	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 10 V, V _{GEN} = 4.5 V, R _G = 3.9 Ω, R _L = 2 Ω, I _D = 5 A	-	8.1	-	nS
t _r	Turn-on Rise Time		-	21.1	-	
t _{d(off)}	Turn-off Delay Time		-	59.1	-	
t _f	Turn-off Fall Time		-	29.3	-	
Gate Charge Characteristics^b						
Q _g	Total Gate Charge	V _{GS} = 4.5 V, V _{DS} = 10 V, I _{DS} = 5 A	-	13.6	-	nC
Q _{gs}	Gate-Source Charge		-	2.85	-	
Q _{gd}	Gate-Drain Charge		-	3.4	-	

Notes :

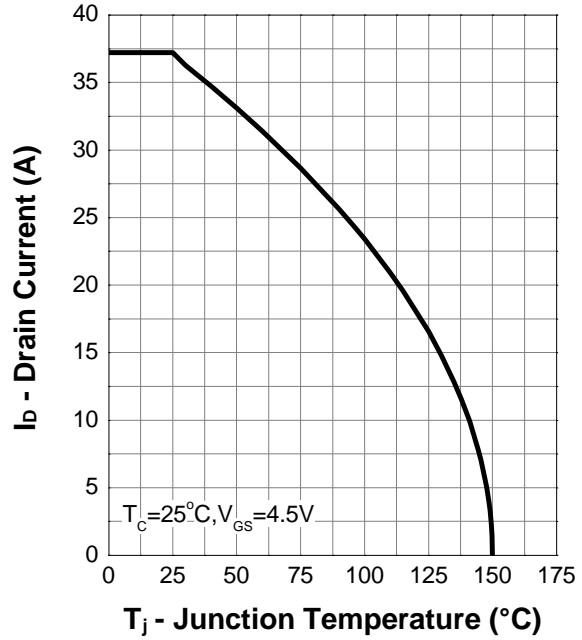
- a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b : Guaranteed by design, not subject to production testing

7. Typical Characteristics (Cont.)

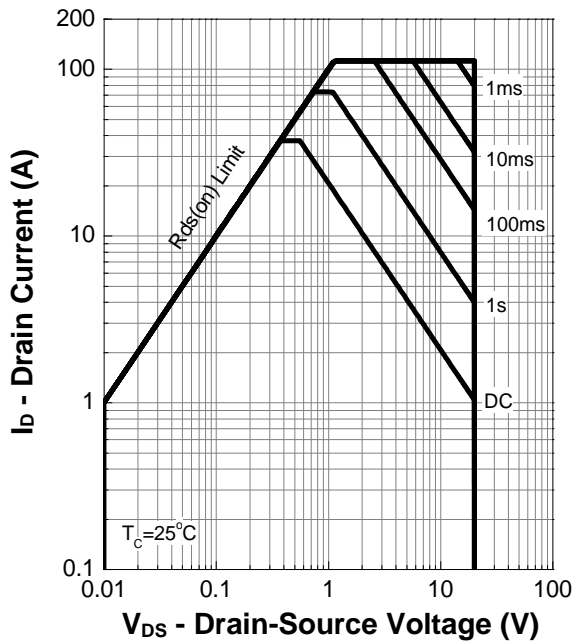
Power Capability



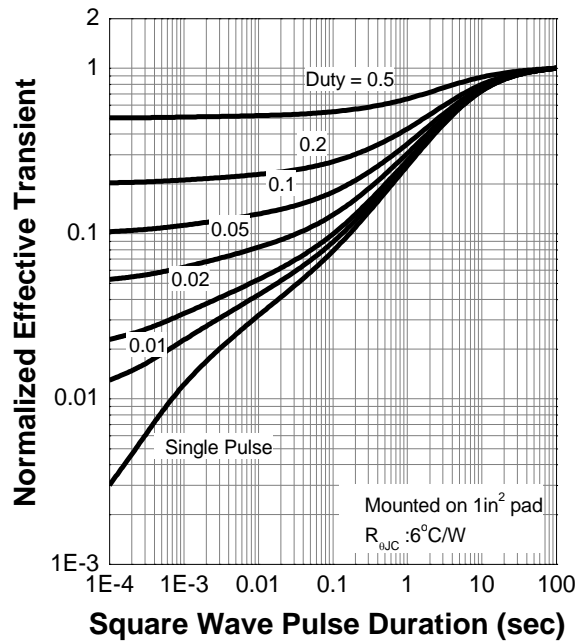
Current Capability



Safe Operating Area



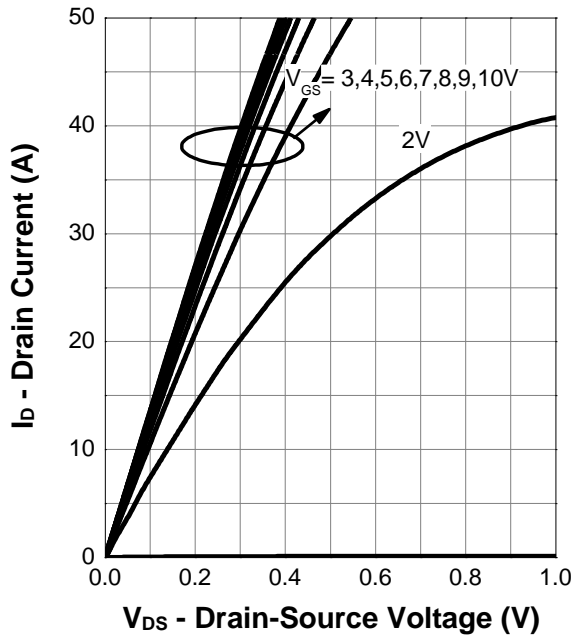
Transient Thermal Impedance



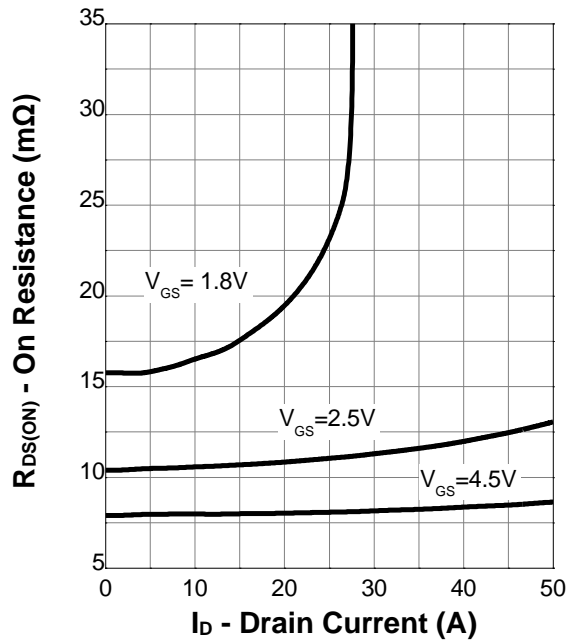


7. Typical Characteristics (Cont.)

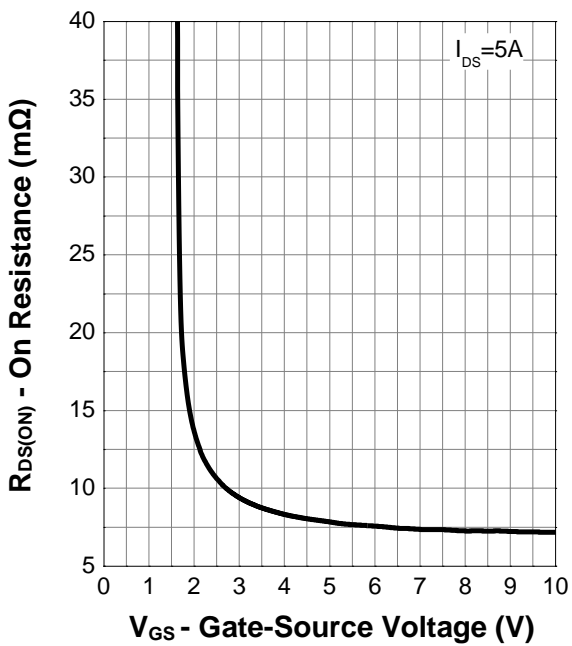
Output Characteristics



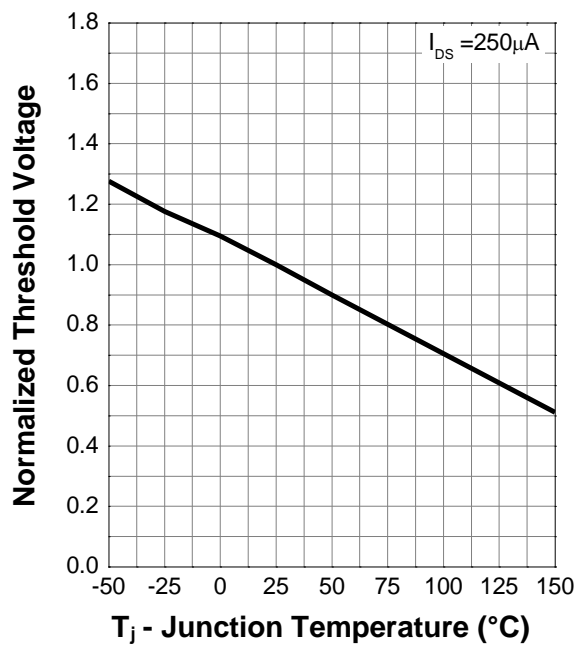
On Resistance



Transfer Characteristics



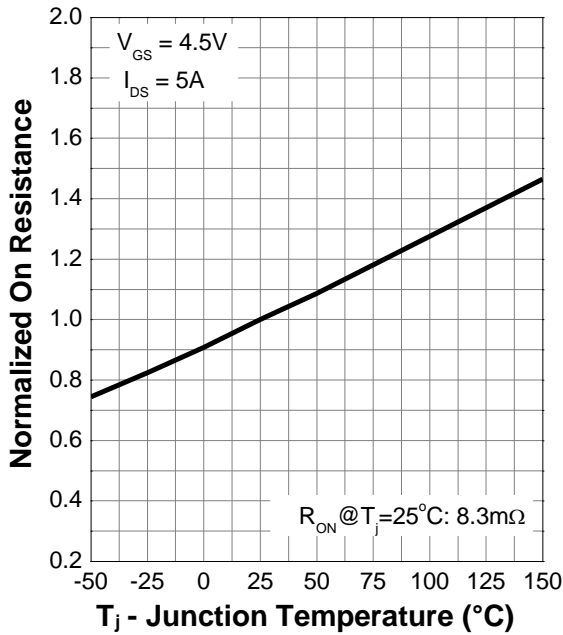
Normalized Threshold Voltage



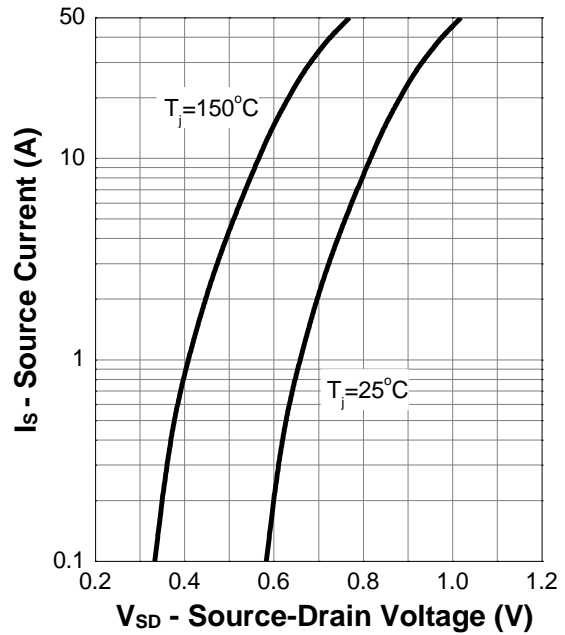


7. Typical Characteristics (Cont.)

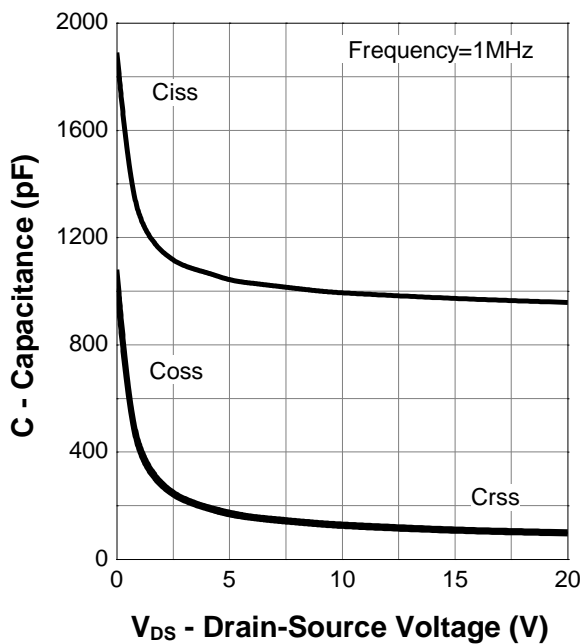
Normalized On Resistance



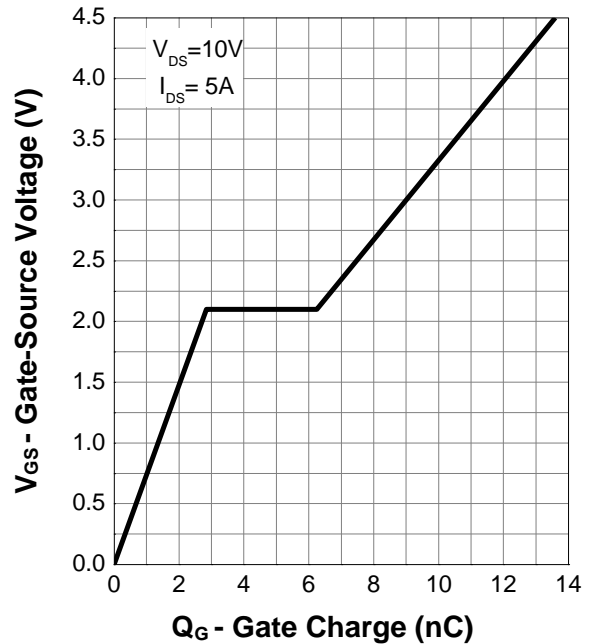
Diode Forward Current



Capacitance



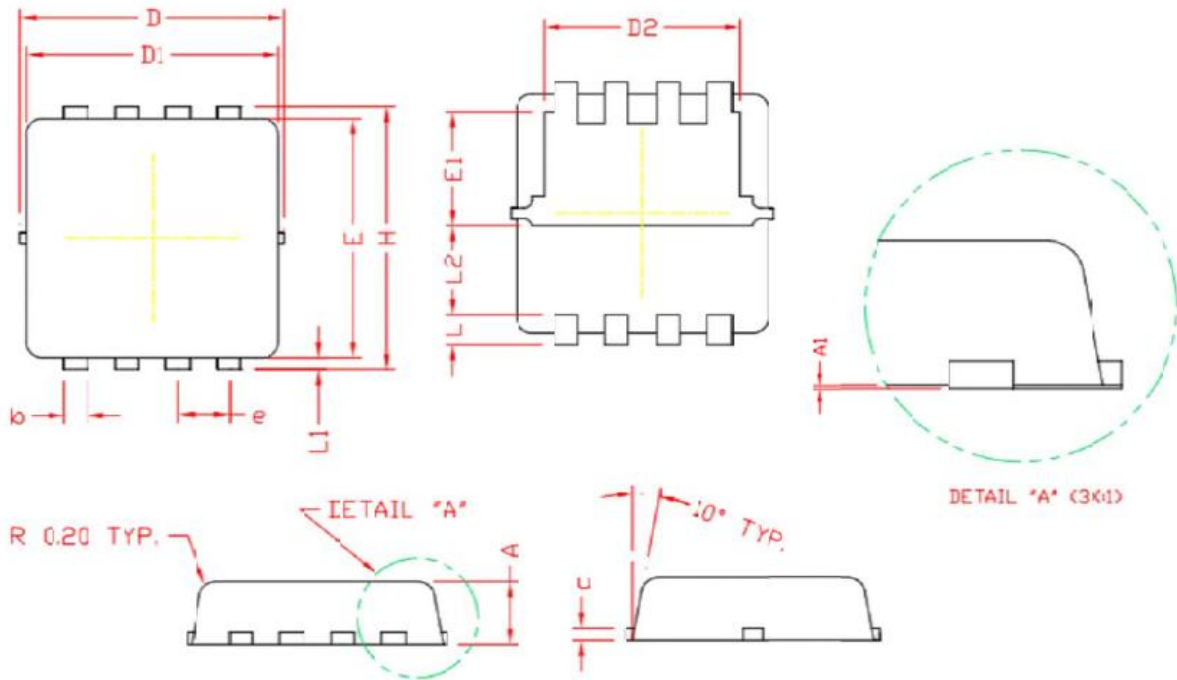
Gate Charge





8. Package Dimensions

PDFN 3.3x3.3-8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.70	0.90
A1	0.00	0.05
b	0.24	0.35
c	0.10	0.20
D	3.25	3.40
D1	3.05	3.25
D2	2.40	2.60
E	3.00	3.20
E1	1.35	1.55
e	0.65 BSC.	
H	3.20	3.40
L	0.30	0.50
L1	0.10	0.20
L2	1.13 REF.	